

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comment s	Error Definition	Errors
1	IS&R	L1	4	(("4701776") or ("4477825")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 15:04			
2	IS&R	L2	2	("20050101152").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 15:49			
3	BRS	L3	8742	(EEPROM or FLOTO or "floating gate tunnel oxide") and etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 15:51			
4	BRS	L4	1559	(EEPROM or FLOTO or "floating gate tunnel oxide") and etch\$3 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 15:52			
5	BRS	L5	651	(EEPROM or FLOTO or "floating gate tunnel oxide") and etch\$3 and LOCOS and (P adj3 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 15:53			
6	BRS	L6	540	5 and @pd<="20040311"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 15:54			
7	BRS	L7	651	(EEPROM or FLOTOX or "floating gate tunnel oxide") and etch\$3 and LOCOS and (P adj3 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 15:53			
8	BRS	L8	369	(EEPROM or FLOTOX or "floating gate tunnel oxide") and etch\$3 and LOCOS and (P adj3 substrate) AND (FOX or "field oxide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 16:25			
9	BRS	L9	335	8 and @pd<="20040311"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 16:22			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
10	BRS	L10	1	(EEPROM or FLOTOX or "floating gate tunnel oxide") and etch\$3 and LOCOS and (P adj3 substrate) AND (FOX or "field oxide") and (tunnel adj3 implant\$3 adj3 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 16:21			
11	BRS	L11	54	(EEPROM or FLOTOX or "floating gate tunnel oxide") and etch\$3 and LOCOS and (P adj3 substrate) AND (FOX or "field oxide") and (tunnel adj3 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 16:21			
12	BRS	L12	47	11 and @pd<="20040311"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 16:26			
13	BRS	L13	117	(EEPROM or FLOTOX or "floating gate tunnel oxide") and etch\$3 and LOCOS and (FOX or "field oxide") and diffus\$3 and (tunnel\$3 adj3 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 16:26			
14	BRS	L14	101	13 and @pd<="20040311"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 17:03			
15	BRS	L15	1	SINOZAWA-MASAHIKO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 17:02			
16	BRS	L16	3273	(etch\$3 same memory same diffus\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 17:03			
17	BRS	L17	236	(etch\$3 same memory same diffus\$3) same tunnel\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 17:03			
18	BRS	L18	166	17 and @pd<="20040311"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/26 17:03			